

Supporting information

Sub-second photo-annealing of solution-processed metal oxide thin-film transistors via irradiation of intensely pulsed white light

Tae-Hee Yoo¹, Seong-Ji Kwon¹, Hak-Sung Kim², Jae-Min Hong¹, Jung Ah Lim^{1,*} and Yong-Won Song^{1,*}

* Authors to whom correspondence should be addressed; electronic mails: jalim@kist.re.kr, ysong@kist.re.kr TEL: +82 29585378; Fax: +82 29585307

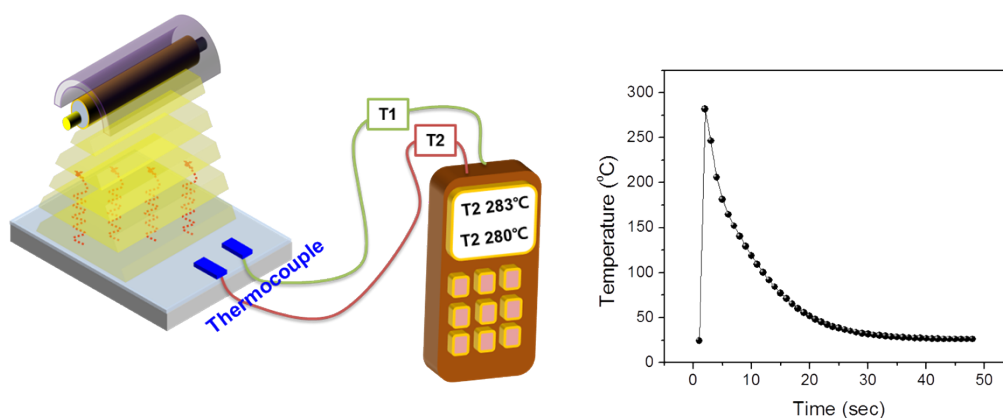
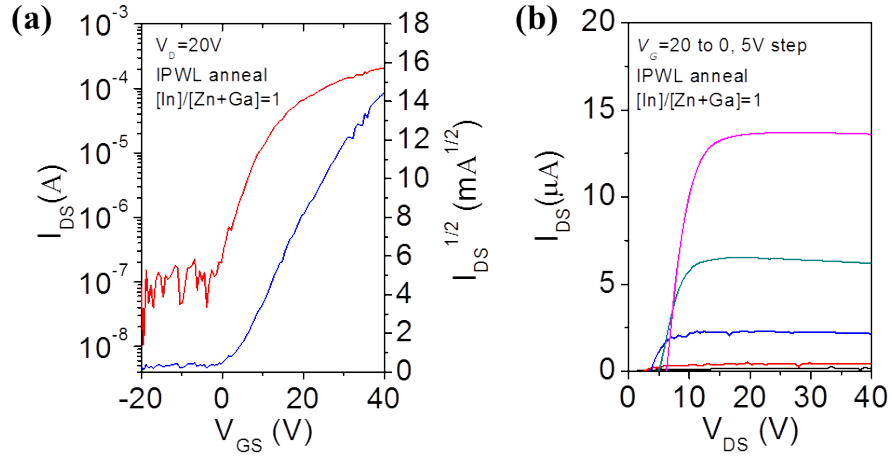


Figure S1. Measurement of the surface temperature during/after IPWL annealing process using thermocouple.



μ_{sat} (cm ² /V·s)	$I_{\text{on}}/I_{\text{off}}$	V_{th} (V)	S.S (V/decade)
0.86	1.74×10^3	0.27	5.4

Figure S2. (a) I_{DS} - V_{GS} and (b) I_{DS} - V_{DS} characteristics of by IPWL-annealed IGZO TFT with different pulse condition. (pulse duration time: 1ms, free temporal period: 30 ms, number of pulses: 70, applied voltage: 330 V)